

Abstract of the Disclosure:

A semiconductor device has an insulating film. An interconnect groove or a via hole is formed in the insulating film. An interconnect pattern or a via hole is buried in the interconnect groove or the via hole. A substantially flat hard mask is formed on the interconnect pattern. The hard mask is provided with an opening portion having a width narrower than a space between adjacent interconnect patterns and is made of a material that is etched selectively with the insulating film.